Logic controlled high-side power switch Rev. 2 — 20 June 2018

Product data sheet

1. General description

The NX3P1108 is a high-side load switch which features a low ON resistance P-channel MOSFET that supports more than 1.5 A of continuous current. It has an integrated output discharge resistor to discharge the output capacitance when disabled. Designed for operation from 0.9 V to 3.6 V, it is used in power domain isolation applications to reduce power dissipation and extend battery life. The enable logic includes integrated logic level translation making the device compatible with lower voltage processors and controllers. The NX3P1108 is ideal for portable, battery operated applications due to low ground current and ultra-low OFF-state current.

2. **Features and benefits**

- Wide supply voltage range from 0.9 V to 3.6 V
- Very low ON resistance:
 - 34 mΩ at a supply voltage of 3.3 V
- High noise immunity
- Low OFF-state leakage current (2.0 μA maximum)
- 1.2 V control logic at a supply voltage of 3.6 V
- High current handling capability (1.5 A continuous current)
- Internal output discharge resistor
- Turn-on slew rate limiting
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 4000 V
 - CDM AEC-Q100-011 revision B exceeds 500 V
- Specified from –40 °C to +85 °C

3. Applications

- Cell phone
- Digital cameras and audio devices
- Portable and battery-powered equipment



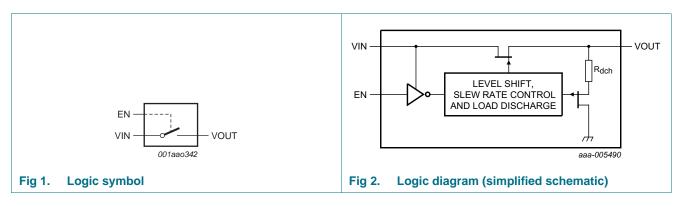
4. Ordering information

Table 1. Ordering information							
Type number	Package						
	Temperature range	Name	Description	Version			
NX3P1108UK	–40 °C to +85 °C	WLCSP4	wafer level chip-scale package; 4 bumps; 0.97 mm x 0.97 mm x 0.54 mm body (backside coating included)	SOT1376-2			

5. Marking

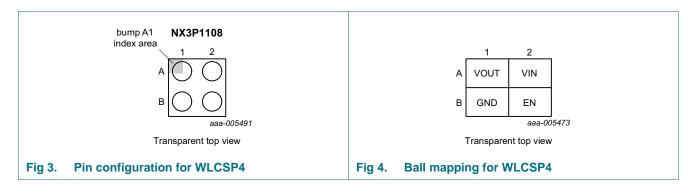
Table 2. Marking codes				
Type number	Marking code			
NX3P1108UK	хВ			

6. Functional diagram



7. Pinning information

7.1 Pinning



NX3P1108

7.2 Pin description

Table 3. Pin description						
Symbol	Pin	Description				
VOUT	A1	output voltage				
GND	B1	ground (0 V)				
VIN	A2	input voltage				
EN	B2	enable input (active HIGH)				

8. Functional description

Table 4.Function table

Input EN	Switch
L	switch OFF
Н	switch ON

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
VI	input voltage	input EN	[1]	-0.5	+4.0	V
		input VIN	[2]	-0.5	+4.0	V
V _{SW}	switch voltage	output VOUT	[2]	-0.5	V _{I(VIN)}	V
l _{IK}	input clamping current	input EN: V _{I(EN)} < -0.5 V		-50	-	mA
I _{SK}	switch clamping current	input VIN: $V_{I(VIN)} < -0.5 V$		-50	-	mA
		output VOUT: $V_{O(VOUT)} < -0.5 V$		-50	-	mA
		output VOUT: $V_{O(VOUT)} > V_{I(VIN)} + 0.5 V$		-	50	mA
I _{SW}	switch current	V_{SW} > -0.5 V		-	±1500	mA
T _{j(max)}	maximum junction temperature			-40	+125	°C
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation		[3]	-	300	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] The (absolute) maximum power dissipation depends on the junction temperature Tj. Higher power dissipation is allowed in conjunction with lower ambient temperatures. The conditions to determine the specified values are $T_{amb} = 85 \text{ °C}$ and the use of a two layer PCB.

10. Recommended operating conditions

Table 6.	Recommended operating conditions						
Symbol	Parameter	Conditions		Min	Max	Unit	
VI	input voltage		(0.9	3.6	V	
T _{amb}	ambient temperature		-	-40	+85	°C	

11. Thermal characteristics

Table 7. **Thermal characteristics**

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1][2]	84	K/W

[1] The overall R_{th(i-a)} can vary depending on the board layout. To minimize the effective R_{th(i-a)}, all pins must have a solid connection to larger Cu layer areas for example, to the power and ground layer. In multi-layer PCB applications, use the second layer to create a large heat spreader area right below the device. If this layer is either ground or power, connect it with several vias to the top layer connected to the device ground or supply. Try not to use any solder-stop varnish under the chip.

[2] Rely on the measurement data given for a rough estimation of the Rth(j-a) in your application. The actual Rth(j-a) value may vary in applications using different layer stacks and layouts

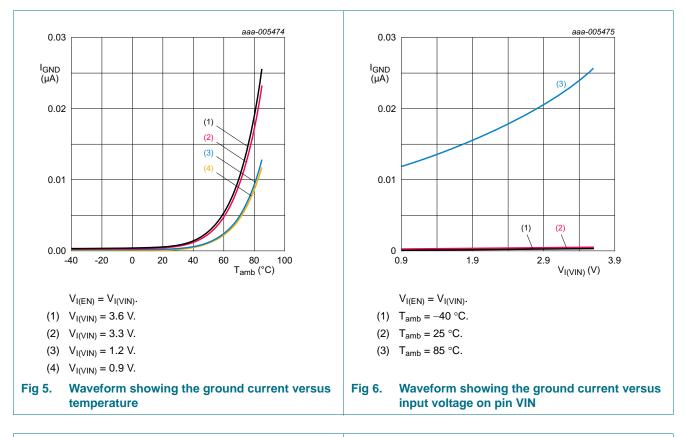
12. Static characteristics

Table 8. **Static characteristics**

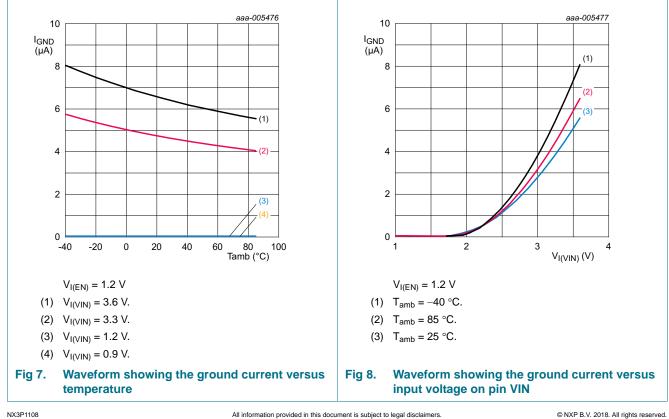
 $V_{I(V(N))} = 0.9 V$ to 3.6 V, unless otherwise specified; Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Ta	_{mb} = 25	°C	$T_{amb} = -40$	Unit	
			Min	Тур	Мах	Min	Max	
V _{IH}	HIGH-level	EN input						
i	input voltage	$V_{I(VIN)} = 0.9 V \text{ to } 1.1 V$	-	-	-	0.8	-	V
		V _{I(VIN)} = 1.1 V to 1.3 V	-	-	-	1.0	-	V
		V _{I(VIN)} = 1.3 V to 1.8 V	-	-	-	1.1	-	V
		V _{I(VIN)} = 1.8 V to 3.6 V	-	-	-	1.1	-	V
V _{IL}	LOW-level input voltage	EN input						
		$V_{I(VIN)} = 0.9 V \text{ to } 1.1 V$	-	-	-	-	0.2	V
		V _{I(VIN)} = 1.1 V to 1.3 V	-	-	-	-	0.3	V
		V _{I(VIN)} = 1.3 V to 1.8 V	-	-	-	-	0.4	V
		V _{I(VIN)} = 1.8 V to 3.6 V	-	-	-	-	0.45	V
I _I	input leakage current	V _{I(EN)} = 0 V or 3.6 V	-	0.1	-	-	1	μA
I _{GND}	ground current	V _{I(EN)} = 0 V or 3.6 V; VOUT open; see <u>Figure 5</u> and <u>Figure 6</u>	-	-	-	-2	-	μA
I _{S(OFF)}	OFF-state leakage current		-	0.1	-	-	2.0	μA
R _{dch}	discharge resistance	VOUT output; V _{I(VIN)} = 3.3 V	-	120	-	-	-	Ω

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12.1 Graphs

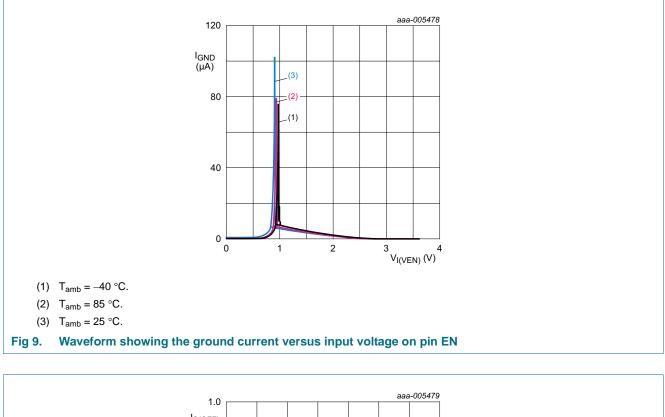


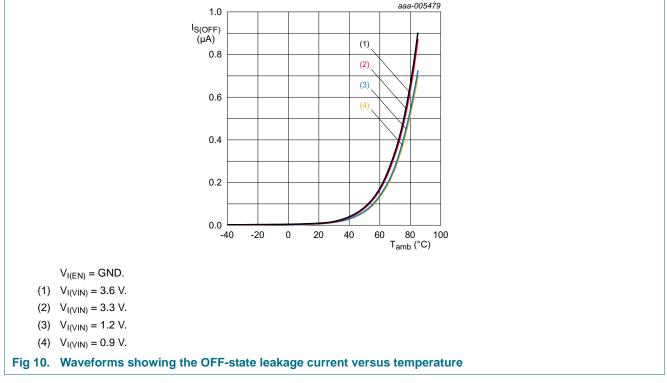
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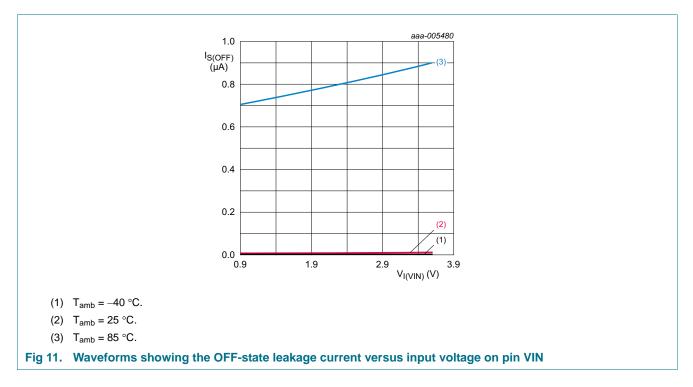
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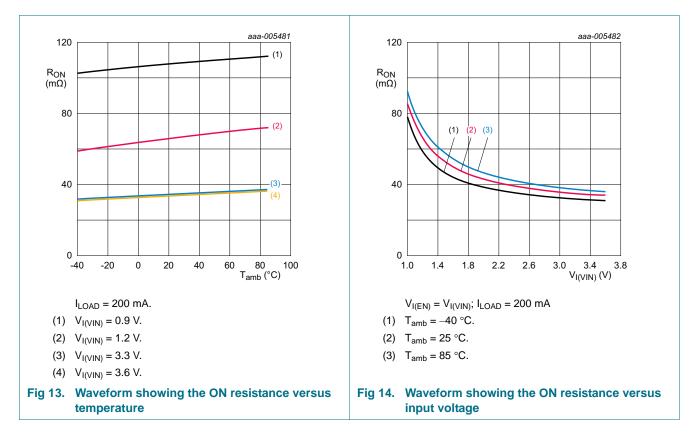
12.2 ON resistance

Table 9. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions			T _{amb} = −40 °C to +85 °C			
				Min	Typ <mark>[1]</mark>	Max		
R _{ON}	ON resistance	$V_{I(EN)} = V_{I(VIN)}$; $I_{LOAD} = 200 \text{ mA}$; see <u>Figure 12</u> , <u>Figure 13</u> and <u>Figure 14</u>						
		V _{I(VIN)} = 0.9 V		-	105	140	mΩ	
		V _{I(VIN)} = 1.2 V		-	68	81	mΩ	
		V _{I(VIN)} = 1.5 V		-	55	65	mΩ	
		V _{I(VIN)} = 1.8 V		-	50	55	mΩ	
		V _{I(VIN)} = 2.5 V		-	40	44	mΩ	
		V _{I(VIN)} = 3.3 V		-	34	40	mΩ	

[1] Typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.



13. Dynamic characteristics

Table 10. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions	1	∫ _{amb} = 25 °	С	Unit
			Min	Тур	Max	
t _{en}	enable time	EN to VOUT; see Figure 15				
		V _{I(VIN)} = 1.8 V	-	120	-	μS
		V _{I(VIN)} = 3.3 V	-	70	-	μS
t _{dis}	disable time	EN to VOUT; see Figure 15				
		V _{I(VIN)} = 1.8 V	-	1.5	-	μS
		V _{I(VIN)} = 3.3 V	-	1.5	-	μS
t _{on} turn-on time	turn-on time	EN to VOUT; see Figure 15				
		V _{I(VIN)} = 1.8 V	-	220	-	μS
		V _{I(VIN)} = 3.3 V	-	150	-	μS
t _{off}	turn-off time	EN to VOUT; see Figure 15				
		V _{I(VIN)} = 1.8 V	-	25	-	μS
		V _{I(VIN)} = 3.3 V	-	22.5	-	μS
t _{TLH}	LOW to HIGH output	VOUT; see Figure 15				
	transition time	V _{I(VIN)} = 1.8 V	-	100	-	μS
		V _{I(VIN)} = 3.3 V	-	80	-	μS
t _{THL}	HIGH to LOW output	VOUT; see Figure 15				
	transition time	V _{I(VIN)} = 1.8 V	-	23.5	-	μS
		V _{I(VIN)} = 3.3 V	-	21	-	μS

13.1 Waveform and test circuits

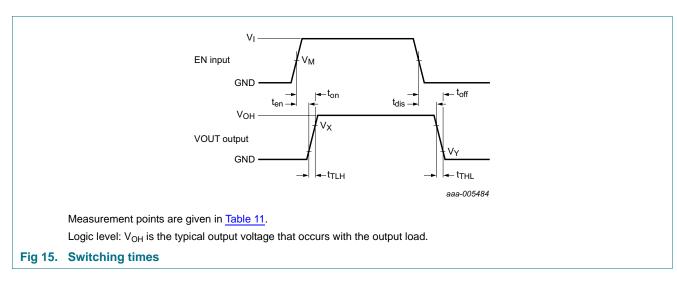


Table 11.Measurement points

Supply voltage	EN Input	Output		
V _{I(VIN)}	V _M	V _X	V _Y	
0.9 V to 3.6 V	$0.5 imes V_I$	$0.9 imes V_{OH}$	$0.1 \times V_{OH}$	

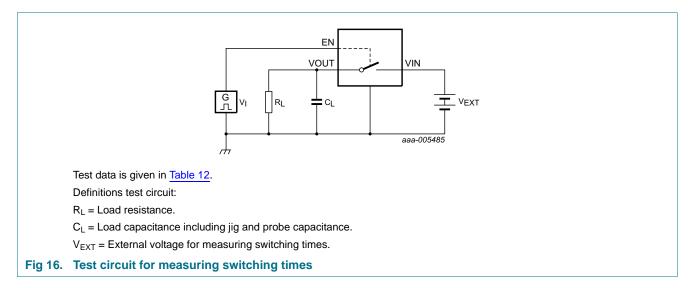
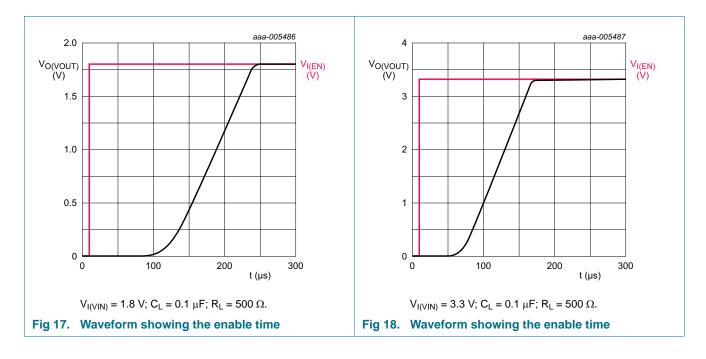


Table 12. Test data

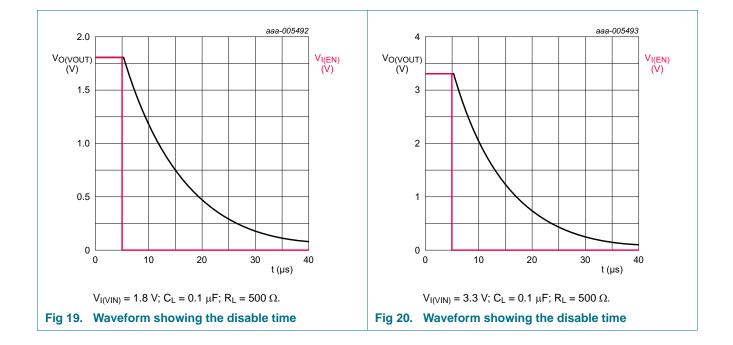
Supply voltage	EN Input	Load		
V _{EXT}	VI	CL	R _L	
0.9 V to 3.6 V	3.3 V	0.1 μF	500 Ω	



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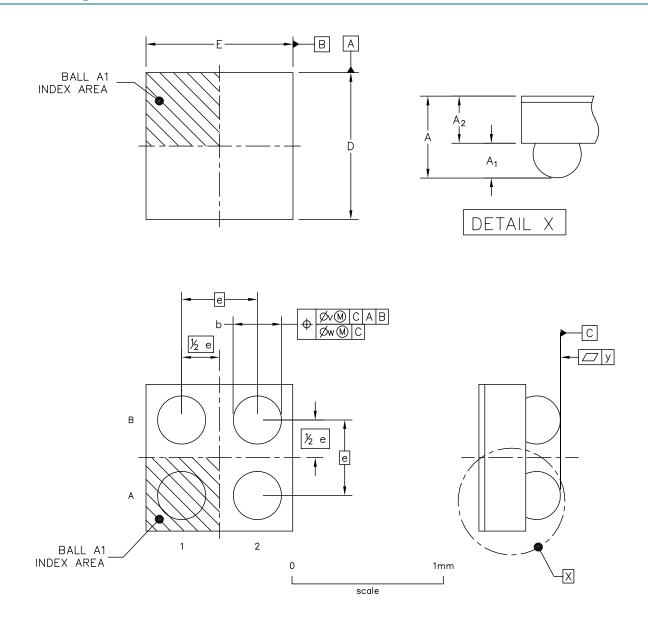
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14. Package outline



DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁	A ₂	b	D	E	е	v	w	у
mm	0.54	0.23	0.335 0.310 0.285	0.32	0.97		0.5	0.02	0.015	0.03

NOTE: Backside coating 40 um

Fig 21. Package outline WLCSP4 (SOT1376-2)

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15. Abbreviations

Table 13. Abbreviations				
Acronym	Description			
CDM	Charged Device Model			
ESD	ElectroStatic Discharge			
НВМ	Human Body Model			
MOSFET	Metal-Oxide Semiconductor Field Effect Transistor			

16. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
NX3P1108 v.2	20180620	Product data sheet	201804021F01	NX3P1108 v.1		
Modifications:	• Figure 21 "Package outline WLCSP4 (SOT1376-2)": Parameter A1 min/nom/max changed from 0.21/0.24/0.27 to 0.20/0.23/0.26.					
NX3P1108 v.1	20130109	Product data sheet	-	-		

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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